**Electronic Supplementary Information:** 

# Photoconductive and supramolecularly engineered organic field-effect transistors based on fibres from donor-acceptor dyads

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#### 1. Experimental methods

The synthesis of HBC-PMI is described elsewhere.<sup>[1]</sup>

HBC-PMI has been dissolved in 1-phenyloctane (Aldrich) with concentrations ranging from 0.02mM to 0.2mM. Solutions have then been mixed with 2-propanol (Carlo Erba) in a 1:1 volume ratio and left to precipitate. Precipitation was slow for this combination of solvents with fibres only becoming visible by eye after more than one day. Additional 2-propanol has been added after more than 2 days to complete precipitation. Bundles of precipitated fibres have been carefully picked up with a pipette and cast on mica/SiO<sub>x</sub>. Samples have then been dried at 70°C in air for at least 12hours.

AFM measurements have been performed in air using a Veeco Dimension 3100 AFM in tapping mode.

KPFM (and the corresponding AFM) images has been recorded using a Multimode IIIA (Veeco) scanning probe microscope with Extender Electronics module. Imaging was done in tapping mode using a conductive SCM-PIT probe (Veeco, Pt/Ir coated Si with frequency  $f_0 = 79$  KHz and nominal tip radius  $\leq 20$  nm). All images were collected under ambient conditions at 10% relative humidity and RT with a scanning raster rate of 1 Hz. The humidity has been measured with a commercial RH meter (Honeywell, HIH-4000-001) having an operating range from 0% to 100% RH with an accuracy of  $\pm 3.5\%$ . KPFM measurements has been acquired in lift mode (lift height = 20 nm,  $V_{AC} = 1000$  mV).

Au electrodes (120nm) have been deposited using TEM grids (Ted Paella Inc, gilder grid 200 Mesh) as a shadow mask. Deposition has been performed in a high vacuum chamber (Plassys,  $p<10^{-6}$ mbar) using resistively heated boat evaporators with the sample being kept at room temperature. The deposition rate (1nm/s) has been monitored using a quartz microbalance. After electrode deposition, samples were immediately transferred inside a glovebox operated under nitrogen atmosphere (O<sub>2</sub><10ppm) for electrical characterization. To exclude any effects of the air exposure on the device properties, some devices have been annealed at 80°C inside the glovebox which did however not lead to a measurable change in the electronic properties.

Devices have been characterized using a Keithley 2636A sourcemeter with biases applied to gate and drain while the source was being connected to the ground. n++-doped silicon

serves as a gate covered with a 230nm thermally grown oxide (Frauenhofer Institute, capacitance  $1.5 \times 10^{-8}$  F/cm<sup>2</sup>).

The light intensity during measurements has been determined using a Thorlabs slim power sensor (S130A). A black curtain was used to reduce stray light inside the glovebox for measurements in the dark (total light intensity  $<0.1\mu$ W/cm<sup>2</sup>). For measurements under illumination, a Leica LED1000 white light OLED ring with 40 white OLEDs was used as a white light source (7mW/cm<sup>2</sup> at sample position).

#### 2. Photoresponse of an OFET based on a spin-coated thin film of HBC-PMI

Figure S1 shows the output characteristics under illumination with white light and in the dark of an OFET based on a spin-coated thin film of HBC-PMI. The device has been prepared on commercial electrodes purchased from the Fraunhofer Institute (www.ipms.fraunhofer.de). Devices have been prepared inside a glovebox by i) spin coating 100  $\mu$ l drop of 0.1mM chloroform solution (500 rpm) on pre-patterned samples (i.e. micro-electrodes on SiOx substrates) and ii) annealing at 80°C for 15 hours. The distance between electrodes and channel width amount to 5 $\mu$ m and 10mm, respectively.



**Figure S1:** Output characteristics of an OFET based on a spin-coated thin film of HBC-PMI under white light illumination (left) and in the dark (right).

### Bibliography

[1] J. M. Mativetsky, M. Kastler, R. C. Savage, D. Gentilini, M. Palma, W. Pisula, K. Müllen, P. Samorì, *Advanced Functional Materials* **2009**, *19*, 2486.